

IRF7473

HEXFET® Power MOSFET

Applications

- Telecom and Data-Com 24 and 48V input DC-DC converters
- Motor Control
- Uninterruptible Power Supply

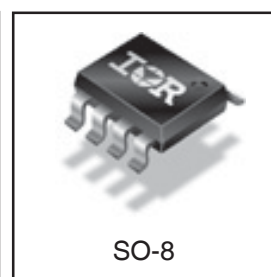
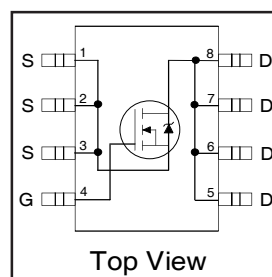
Benefits

- Ultra Low On-Resistance
- High Speed Switching
- Low Gate Drive Current Due to Improved Gate Charge Characteristic
- Improved Avalanche Ruggedness and Dynamic dv/dt
- Fully Characterized Avalanche Voltage and Current

Typical SMPS Topologies

- Full and Half Bridge 48V input Circuit
- Forward 24V input Circuit

V_{DSS}	$R_{DS(on) \text{ max}}$	I_D
100V	$26m\Omega @ V_{GS} = 10V$	6.9A



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	6.9	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.5	
I_{DM}	Pulsed Drain Current ①	55	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ⑥	5.8	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④	—	50	

Notes ① through ⑥ are on page 8
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IRF7473

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/°C	Reference to 25°C , $I_D = 1mA$ ③
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	22	26	mΩ	$V_{GS} = 10V, I_D = 4.1A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.5	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 95V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

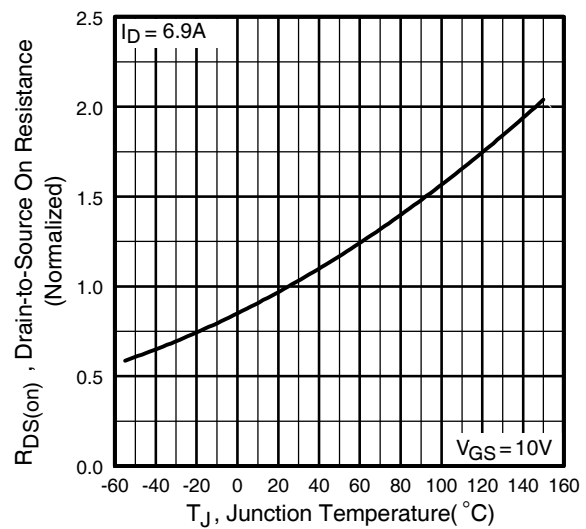
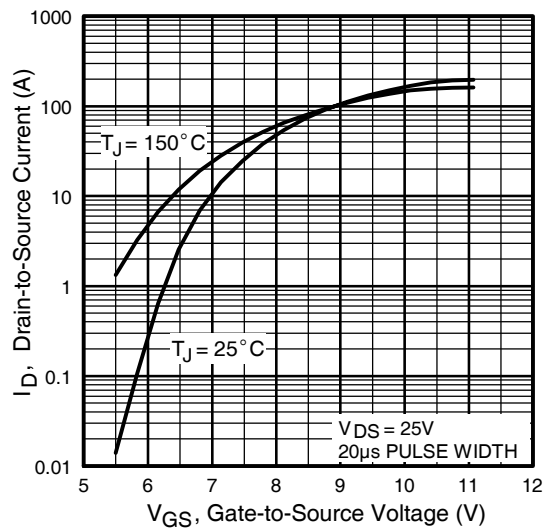
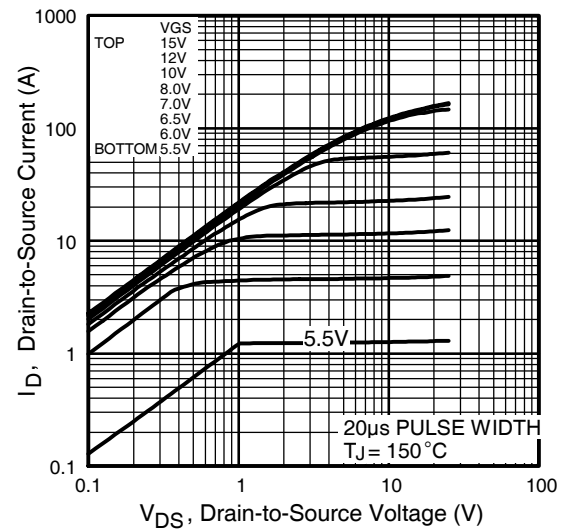
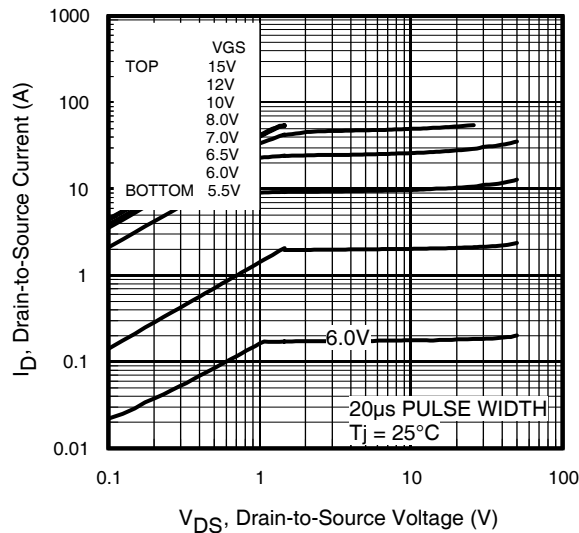
	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	10	—	—	S	$V_{DS} = 50V, I_D = 4.1A$
Q_g	Total Gate Charge	—	61	—	nC	$I_D = 4.1A$
Q_{gs}	Gate-to-Source Charge	—	21	—		$V_{DS} = 50V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	19	—		$V_{GS} = 10V,$
$t_{d(on)}$	Turn-On Delay Time	—	24	—	ns	$V_{DD} = 50V$
t_r	Rise Time	—	20	—		$I_D = 4.1A$
$t_{d(off)}$	Turn-Off Delay Time	—	29	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	11	—		$V_{GS} = 10V$ ③
C_{iss}	Input Capacitance	—	3180	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	230	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	120	—		$f = 1.0MHz$
C_{oss}	Output Capacitance	—	830	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	150	—		$V_{GS} = 0V, V_{DS} = 80V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	230	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	140	mJ
I_{AR}	Avalanche Current①	—	4.1	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	55		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 4.1A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	55	—	ns	$T_J = 25^\circ\text{C}, I_F = 4.1A$
Q_{rr}	Reverse Recovery Charge	—	140	—	nC	$di/dt = 100A/\mu s$ ③



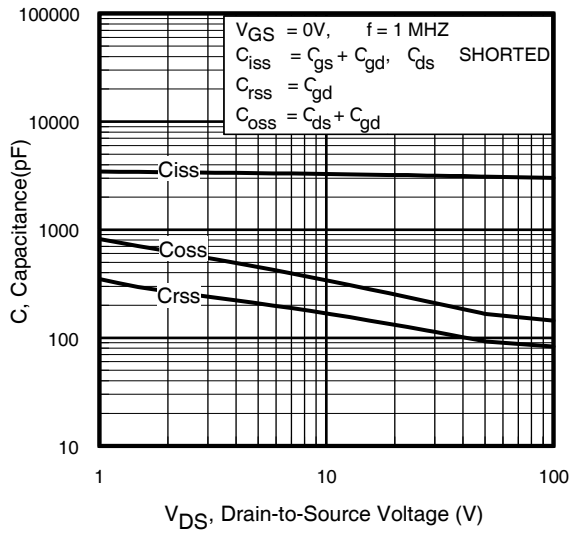


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

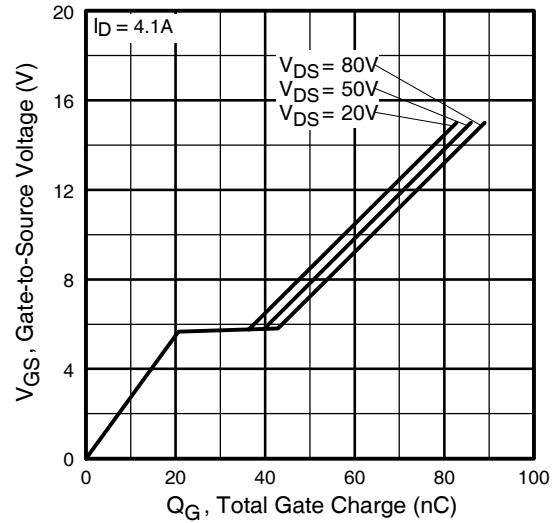


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

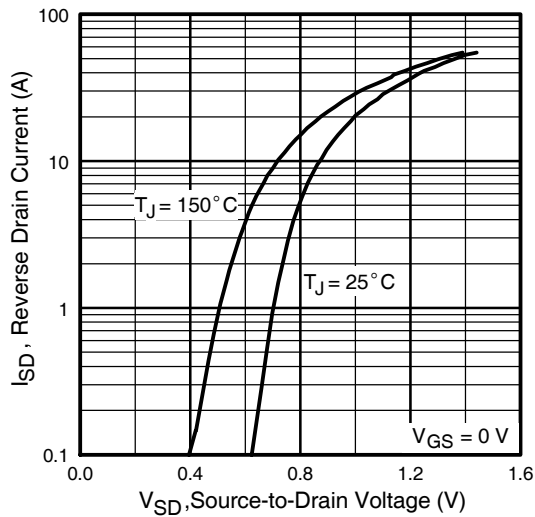


Fig 7. Typical Source-Drain Diode Forward Voltage

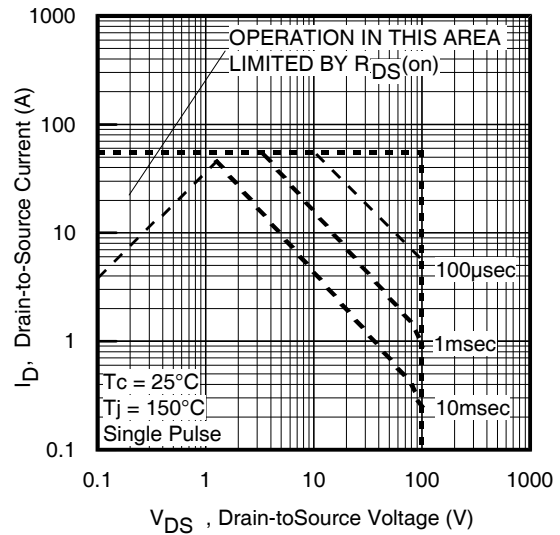


Fig 8. Maximum Safe Operating Area

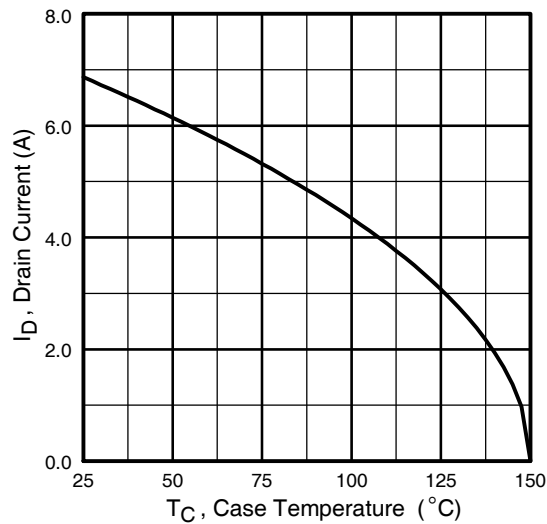


Fig 9. Maximum Drain Current Vs. Ambient Temperature

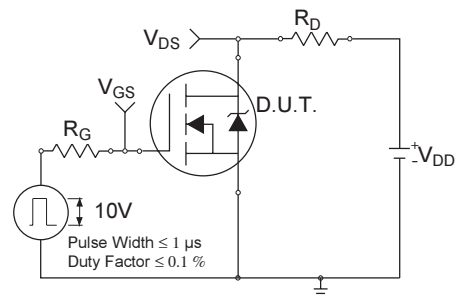


Fig 10a. Switching Time Test Circuit

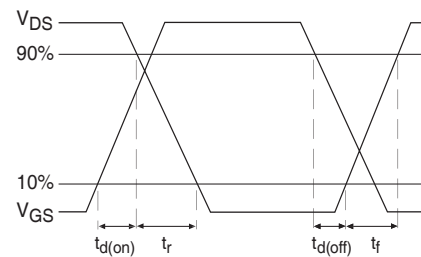


Fig 10b. Switching Time Waveforms

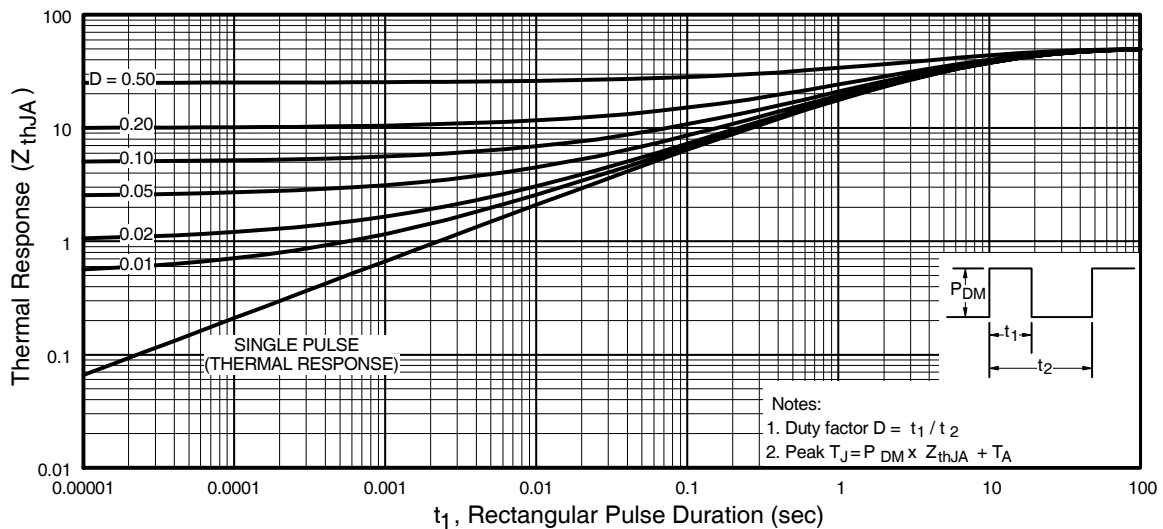


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

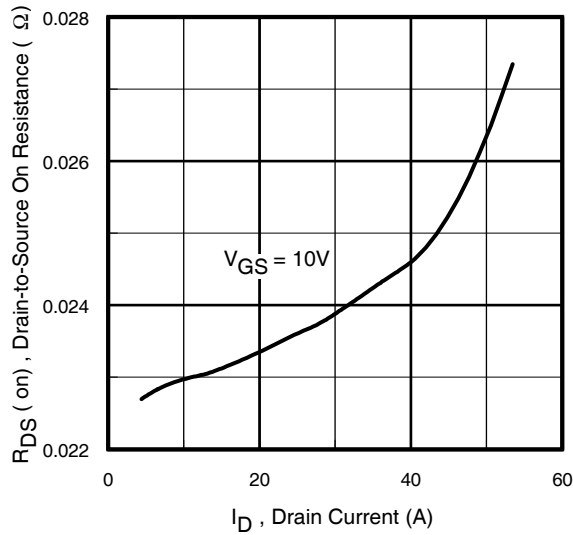


Fig 12. On-Resistance Vs. Drain Current

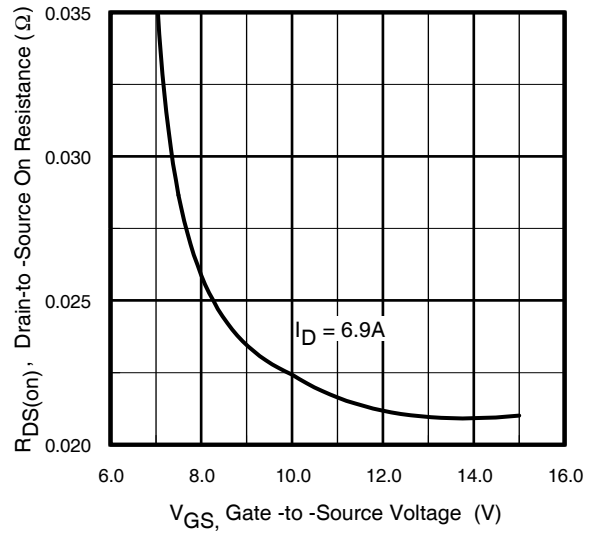


Fig 13. On-Resistance Vs. Gate Voltage

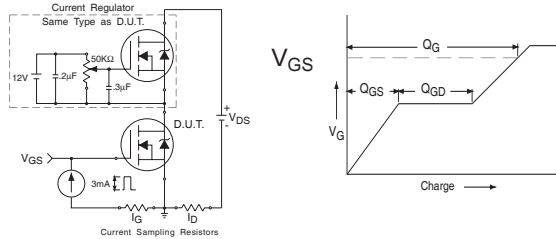


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

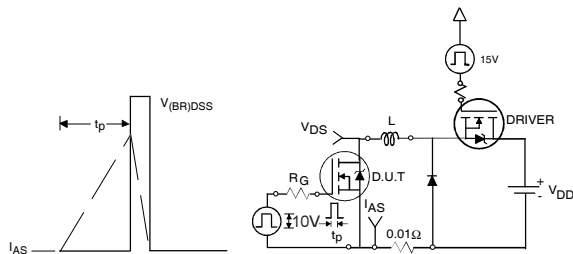


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

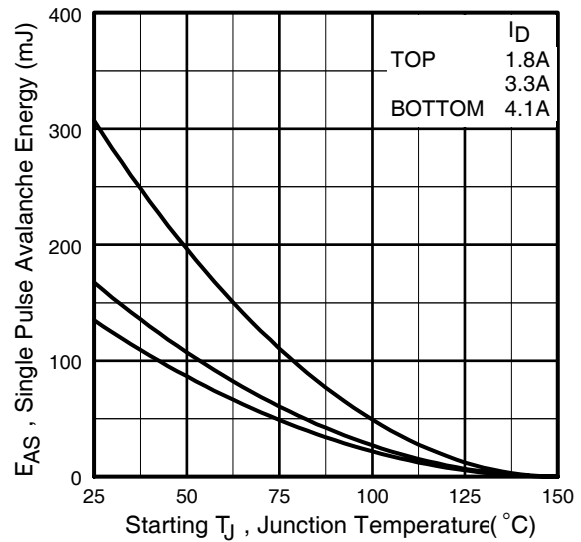
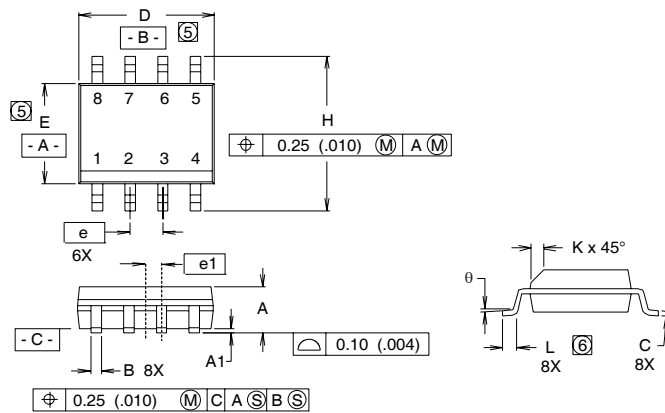


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Details

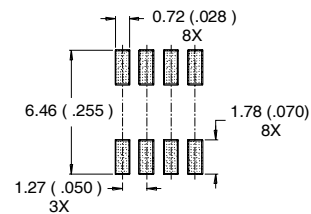


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

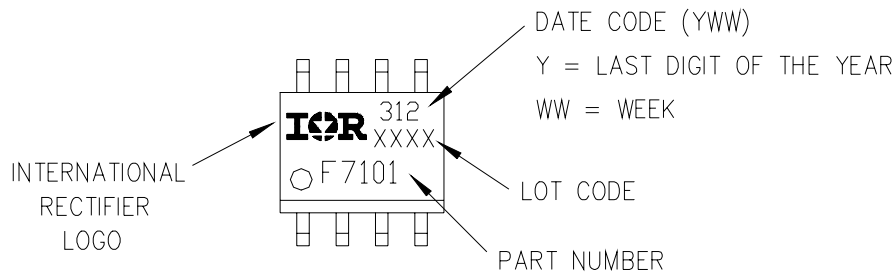
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

RECOMMENDED FOOTPRINT



SO-8 Part Marking

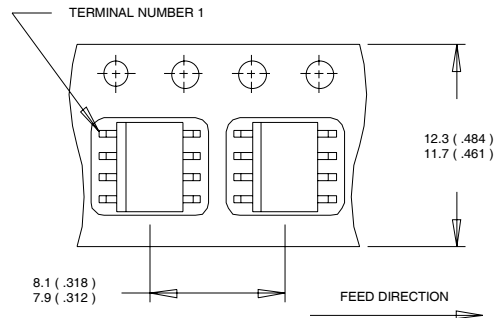
EXAMPLE: THIS IS AN IRF7101



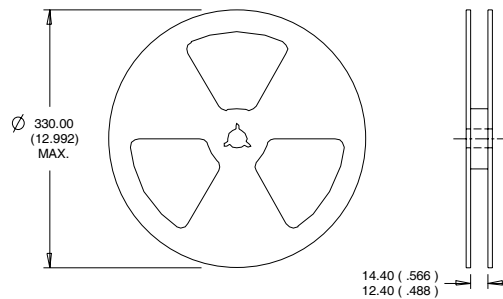
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SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 16\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 4.1\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board
- ⑤ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS}
- ⑥ $I_{SD} \leq 4.1\text{A}$, $di/dt \leq 210\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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